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INTERNATIONAL ELECTROTECHNICAL COMMISSION

SEMICONDUCTOR DEVICES –

Part 16-1: Microwave integrated circuits – Amplifiers

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This Consolidated version of IEC 60747-16-1 bears the edition number 1.2. It consists of the first edition (2001-11) [documents 47E/200/FDIS and 47E/204/RVD], its amendment 1 (2007-01) [documents 47E/305/FDIS and 47E/317/RVD] and its amendment 2 (2017-02) [documents 47E/500/CDV and 47E/518/RVC]. The technical content is identical to the base edition and its amendments.

This Final version does not show where the technical content is modified by amendments 1 and 2. A separate Redline version with all changes highlighted is available in this publication.

International Standard IEC 60747-16-1 has been prepared by subcommittee 47E: Discrete semiconductor devices, of IEC technical committee 47: Semiconductor devices.

The French version of this standard has not been voted upon.

This publication has been drafted in accordance with the ISO/IEC Directives, Part 3.

The committee has decided that the contents of the base publication and its amendments will remain unchanged until the stability date indicated on the IEC web site under "http://webstore.iec.ch" in the data related to the specific publication. At this date, the publication will be

- reconfirmed,
- withdrawn,
- replaced by a revised edition, or
- amended.

SEMICONDUCTOR DEVICES –

Part 16-1: Microwave integrated circuits – Amplifiers

1 Scope

This part of IEC 60747 provides the terminology, the essential ratings and characteristics, as well as the measuring methods for integrated circuit microwave power amplifiers.

2 Normative references

The following normative documents contain provisions which, through reference in this text, constitute provisions of this part of IEC 60747. For dated references, subsequent amendments to, or revisions of, any of these publications do not apply. However, parties to agreements based on this part of IEC 60747 are encouraged to investigate the possibility of applying the most recent editions of the normative documents indicated below. For undated references, the latest edition of the normative document referred to applies. Members of IEC and ISO maintain registers of currently valid International Standards.

IEC 60050-702, *International Electrotechnical Vocabulary – Chapter 702: Oscillations, signals and related devices* (available at: http://www.electropedia.org)

IEC 60617, *Graphical symbols for diagrams* (available at: <http://std.iec.ch/iec60617>)

IEC 60747-1:2006, *Semiconductor devices – Part 1: General*
IEC 60747-1:2006/AMD1:2010

IEC 60747-4:2007, *Semiconductor devices – Discrete devices – Part 4: Microwave diodes and transistors*
IEC 60747-4:2007/AMD1:2017

IEC 60748-2:1997, *Semiconductor devices – Integrated circuits – Part 2: Digital integrated circuits*

IEC 60748-3:1986, *Semiconductor devices – Integrated circuits – Part 3: Analogue integrated circuits*
IEC 60748-3:1986/AMD1:1991
IEC 60748-3:1986/AMD2:1994

IEC 60748-4:1997, *Semiconductor devices – Integrated circuits – Part 4: Interface integrated circuits*

IEC/TS 61340-5-1*, Electrostatics - Part 5-1: Protection of electronic devices from electrostatic phenomena - General requirements*

IEC/TS 61340-5-2*, Electrostatics - Part 5-2: Protection of electronic devices from electrostatic phenomena - User guide*

3 Terms and definitions

For the purposes of this document, the following terms and definitions apply.